

DOCKET NO. 8229-006-27



#5/A
MA
4/4/25/02

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

IN RE APPLICATION OF: T. FRANK WANG

ART UNIT: 1765

SERIAL NO.: 09/609,387

EXAMINER: PEREZ, R.

FILING DATE: JULY 3, 2000

FOR: METHOD OF UNIFORMLY ETCHING REFRactory METALS,
REFRACTORY METAL ALLOYS AND REFRACTORY METAL
SILICIDES

AMENDMENT

ASSISTANT COMMISSIONER FOR PATENTS
WASHINGTON, D.C. 20231

SIR:

RECEIVED
APR 25 2002
TC 1700

Responsive to the outstanding Office Action issued October 25, 2001 (Paper No. 3) and in light of the agreement arrived at during the interview with SPE Utech on January 29, 2002, an extension of time in which to respond to the outstanding Office Action having been secured by the petition and extension fees submitted herewith, entry of the following amendments is respectfully requested.

IN THE CLAIMS

Please amend the claims as follows:

Subj

1. A method for etching a semiconductor device to form an etched pattern therein,

comprising:

- (a) providing a semiconductor device having a plurality of layers, at least one of the layers of the semiconductor device comprising a refractory metal-containing material; and
- (b) etching the semiconductor device under conditions with an etchant composition comprising a first etchant chemistry which comprises a chlorine source and a second etchant chemistry which is free of fluorine.

A1